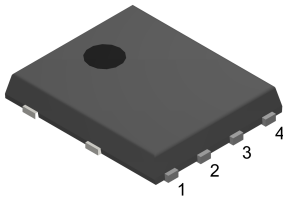
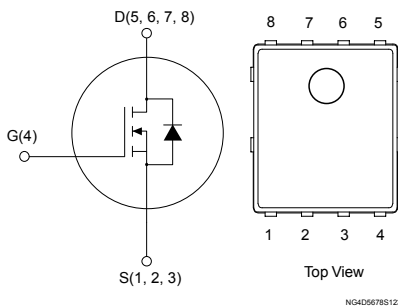


## N-channel 80 V, 5.2 mΩ typ., 100 A, STripFET F7 Power MOSFET in a PowerFLAT 5x6 package


**PowerFLAT 5x6**


### Features

Order code	$V_{DS}$	$R_{DS(on) \max}$	$I_D$	$P_{TOT}$
STL100N8F7	80 V	6.1 mΩ	100 A	120 W

- Among the lowest  $R_{DS(on)}$  on the market
- Excellent FoM (figure of merit)
- Low  $C_{rSS}/C_{iSS}$  ratio for EMI immunity
- High avalanche ruggedness

### Applications

- Switching applications

### Description

This N-channel Power MOSFET utilizes STripFET F7 technology with an enhanced trench gate structure that results in very low on-state resistance, while also reducing internal capacitance and gate charge for faster and more efficient switching.



#### Product status link

[STL100N8F7](#)

#### Product summary

<b>Order code</b>	STL100N8F7
<b>Marking</b>	100N8F7
<b>Package</b>	PowerFLAT 5x6
<b>Packing</b>	Tape and reel

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	80	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	100	A
$I_D^{(1)}$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	71	A
$I_{DM}^{(2)(1)}$	Drain current (pulsed)	400	A
$I_D^{(3)}$	Drain current (continuous) at $T_{pcb} = 25\text{ }^\circ\text{C}$	20	A
$I_D^{(3)}$	Drain current (continuous) at $T_{pcb} = 100\text{ }^\circ\text{C}$	14	A
$I_{DM}^{(3)(2)}$	Drain current (pulsed)	80	A
$P_{TOT}^{(1)}$	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	120	W
$P_{TOT}^{(3)}$	Total power dissipation at $T_{pcb} = 25\text{ }^\circ\text{C}$	4.8	W
$E_{AS}^{(4)}$	Single pulse avalanche energy	220	mJ
$T_J$	Operating junction temperature range	-55 to 175	$^\circ\text{C}$
$T_{stg}$	Storage temperature range		$^\circ\text{C}$

1. This value is rated according to  $R_{thj-c}$ .
2. Pulse width limited by safe operating area.
3. This value is rated according to  $R_{thj-pcb}$ .
4. Starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $I_D = 25\text{ A}$ ,  $V_{DD} = 40\text{ V}$

**Table 2. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	1.25	$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	31.3	$^\circ\text{C/W}$

1. When mounted on FR-4 board of  $1\text{ inch}^2$ , 2oz Cu,  $t < 10\text{ s}$ .

## 2 Electrical characteristics

( $T_C = 25\text{ }^\circ\text{C}$  unless otherwise specified)

**Table 3. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0, I_D = 250\text{ }\mu\text{A}$	80			V
$I_{DSS}$	Zero gate voltage drain current	$V_{GS} = 0, V_{DS} = 80\text{ V}$			1	$\mu\text{A}$
		$V_{GS} = 0, V_{DS} = 80\text{ V},$ $T_C = 125\text{ }^\circ\text{C}^{(1)}$			10	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.5		4.5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 10\text{ A}$		5.2	6.1	m $\Omega$

1. Defined by design, not subject to production test.

**Table 4. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{GS} = 0, V_{DS} = 40\text{ V}, f = 1\text{ MHz}$	-	3435	-	pF
$C_{oss}$	Output capacitance		-	653	-	pF
$C_{riss}$	Reverse transfer capacitance		-	57	-	pF
$Q_g$	Total gate charge	$V_{DD} = 40\text{ V}, I_D = 20\text{ A},$	-	46.8	-	nC
$Q_{gs}$	Gate-source charge	$V_{GS} = 0\text{ to }10\text{ V}$	-	23.4	-	nC
$Q_{gd}$	Gate-drain charge	(see Figure 13. Test circuit for gate charge behavior)	-	11.2	-	nC

**Table 5. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 40\text{ V}, I_D = 10\text{ A}, R_G = 4.7\text{ }\Omega,$ $V_{GS} = 10\text{ V}$	-	49	-	ns
$t_r$	Rise time		-	95	-	ns
$t_{d(off)}$	Turn-off delay time	(see Figure 12. Test circuit for resistive load switching times and Figure 17. Switching time waveform)	-	60	-	ns
$t_f$	Fall time		-	32	-	ns

**Table 6. Source-drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{SD}^{(1)}$	Forward on voltage	$V_{GS} = 0, I_{SD} = 20 \text{ A}$	-		1.2	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 20 \text{ A}, di/dt = 100 \text{ A}/\mu\text{s},$	-	48.6		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 60 \text{ V}$ (see Figure 14. Test circuit for inductive load switching and diode recovery times.	-	58.6		nC
$I_{RRM}$	Reverse recovery current		-	2.4		A

1. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

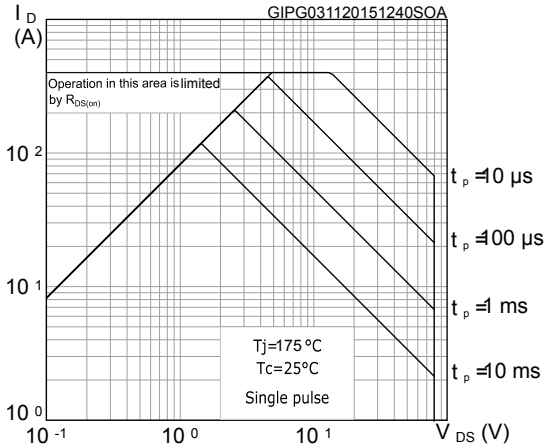


Figure 2. Thermal impedance

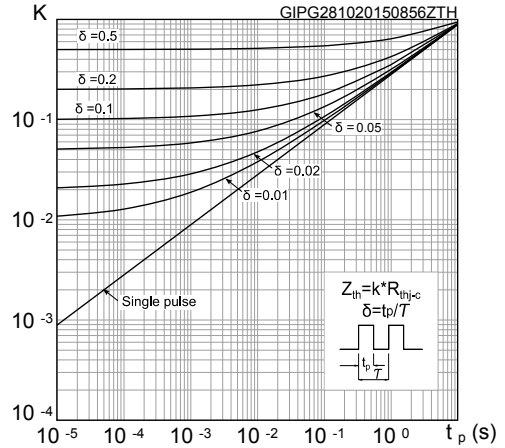


Figure 3. Output characteristics

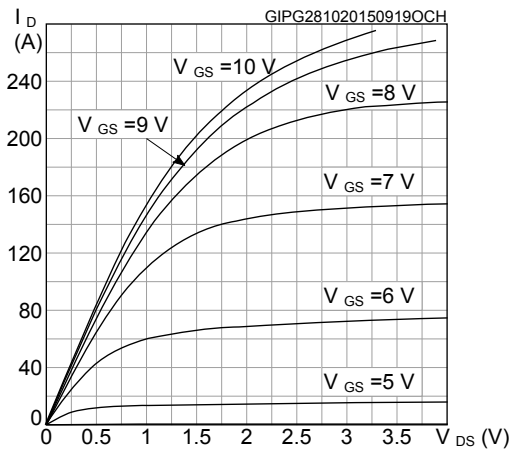


Figure 4. Transfer characteristics

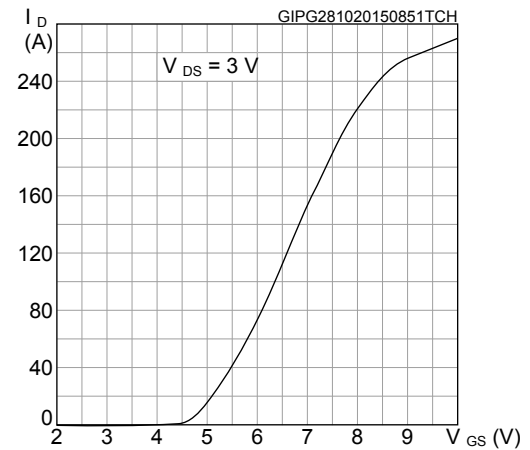


Figure 5. Gate charge vs gate-source voltage

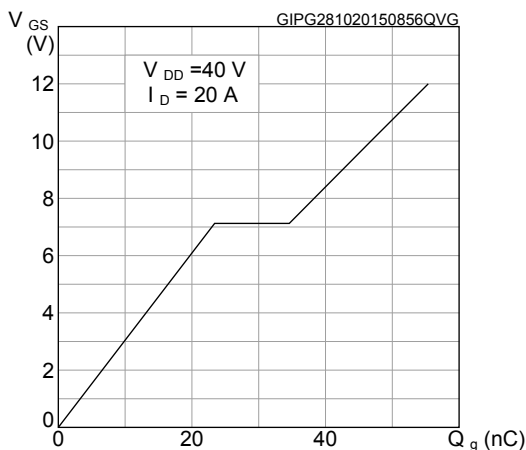


Figure 6. Static drain-source on-resistance

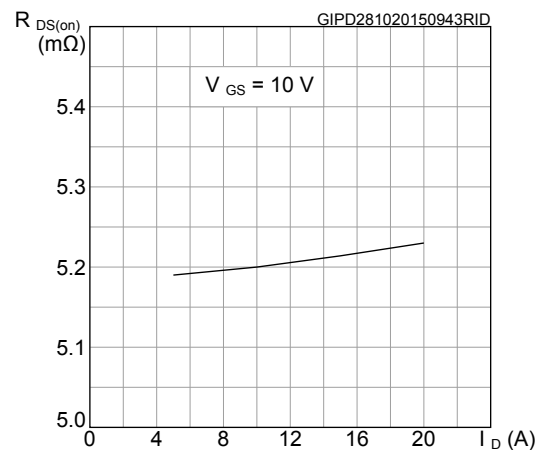


Figure 7. Capacitance variations

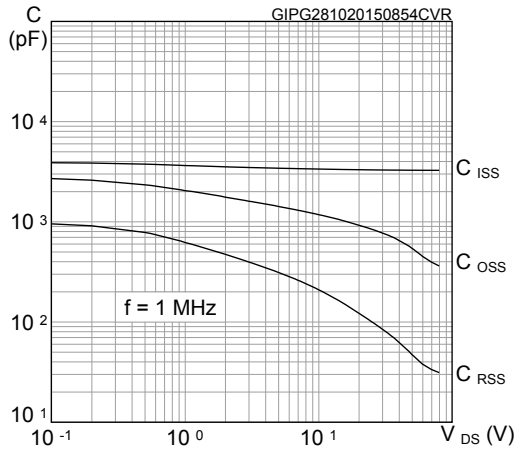


Figure 8. Normalized gate threshold voltage vs temperature

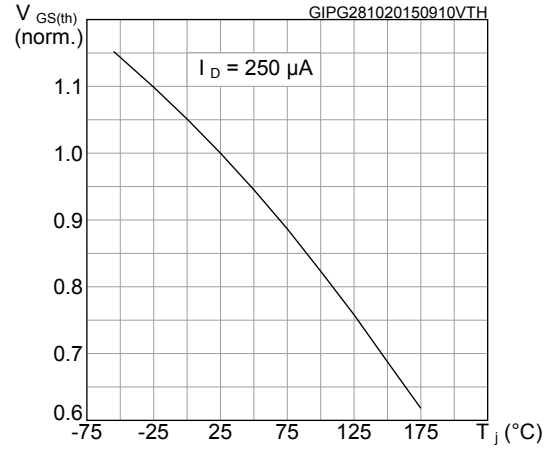


Figure 9. Normalized on-resistance vs temperature

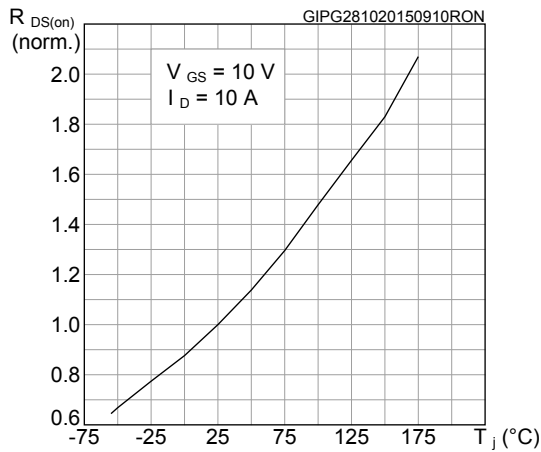


Figure 10. Normalized  $V_{(BR)DSS}$  vs temperature

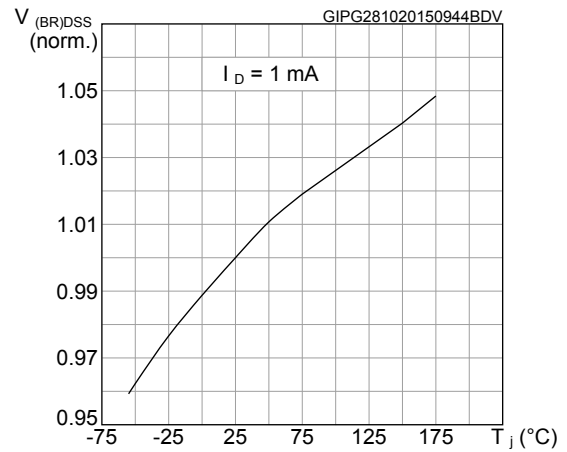
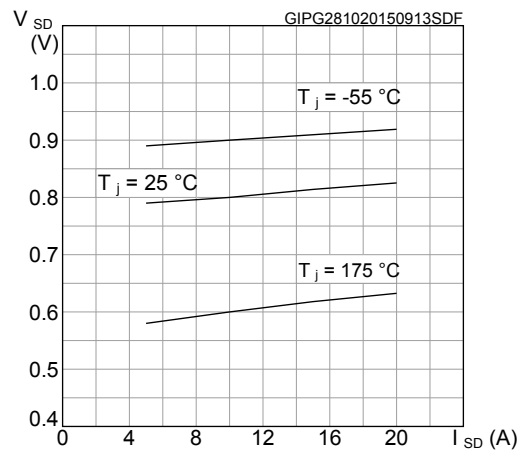
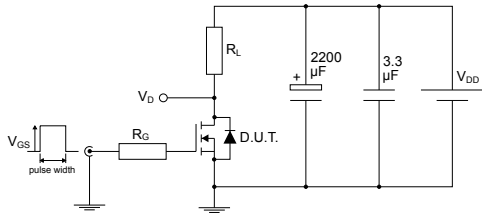


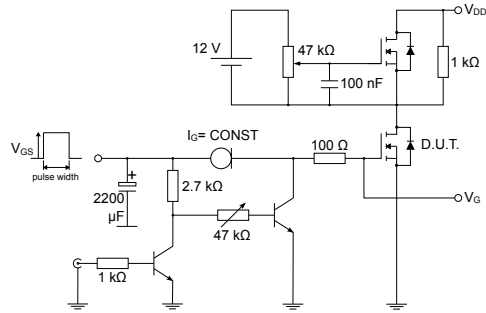
Figure 11. Source-drain diode forward characteristics



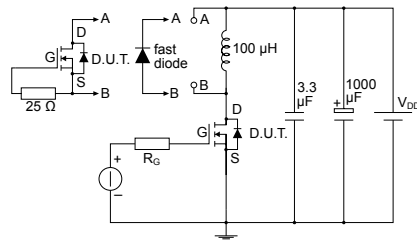
### 3 Test circuits

**Figure 12. Test circuit for resistive load switching times**


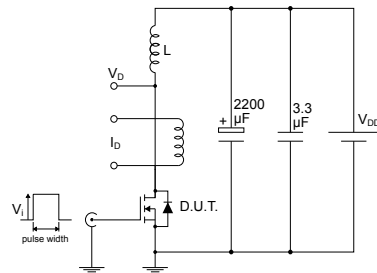
AM01468v1

**Figure 13. Test circuit for gate charge behavior**


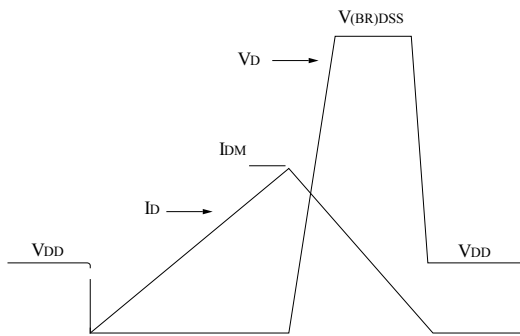
AM01469v1

**Figure 14. Test circuit for inductive load switching and diode recovery times**


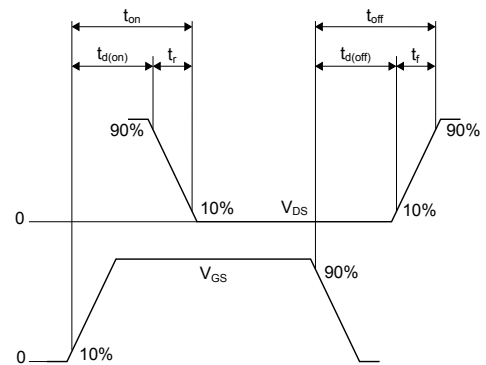
AM01470v1

**Figure 15. Unclamped inductive load test circuit**


AM01471v1

**Figure 16. Unclamped inductive waveform**


AM01472v1

**Figure 17. Switching time waveform**


AM01473v1

## 4 Package information

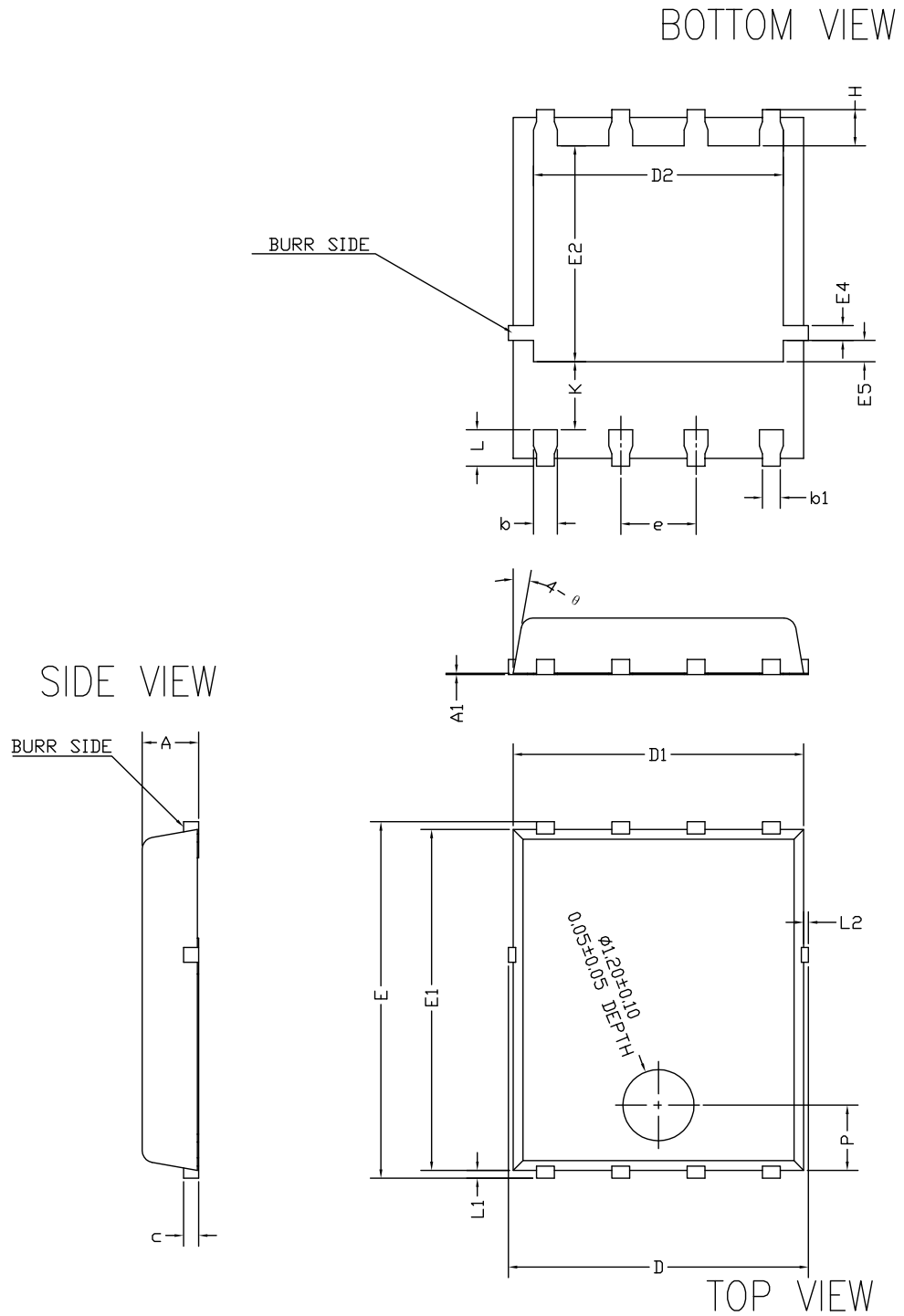
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In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.



### 4.1 PowerFLAT 5x6 type C SUBCON package information

Figure 18. PowerFLAT 5x6 type C SUBCON package outline



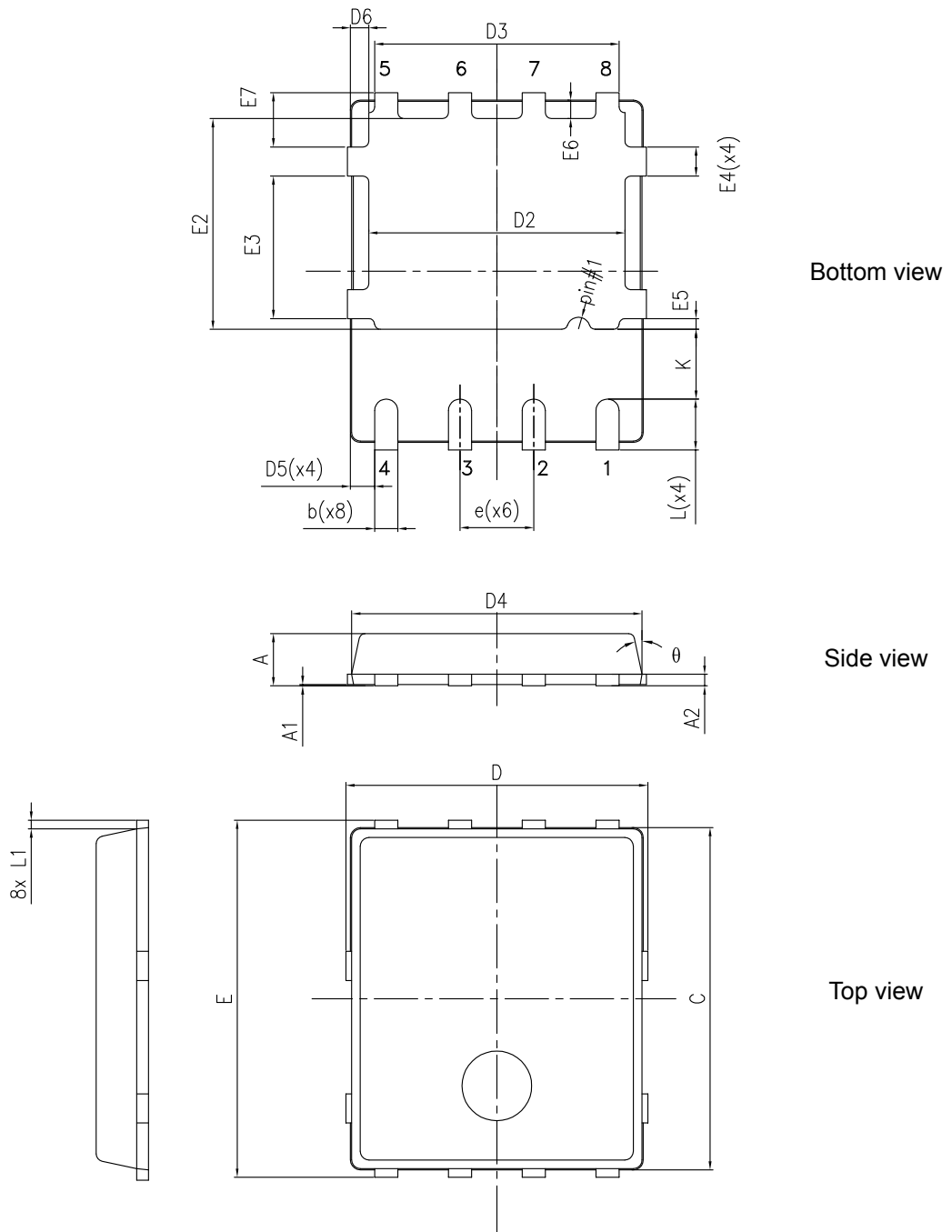
8472137\_SUBCON\_998G\_REV4

**Table 7. PowerFLAT 5x6 type C SUBCON package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	0.90	0.95	1.00
A1		0.02	
b	0.35	0.40	0.45
b1		0.30	
c	0.21	0.25	0.34
D			5.10
D1	4.80	4.90	5.00
D2	4.01	4.21	4.31
e	1.17	1.27	1.37
E	5.90	6.00	6.10
E1	5.70	5.75	5.80
E2	3.54	3.64	3.74
E4	0.15	0.25	0.35
E5	0.26	0.36	0.46
H	0.51	0.61	0.71
K	0.95		
L	0.51	0.61	0.71
L1	0.06	0.13	0.20
L2			0.10
P	1.00	1.10	1.20
θ	8°	10°	12°

## 4.2 PowerFLAT 5x6 type C package information

Figure 19. PowerFLAT 5x6 type C package outline

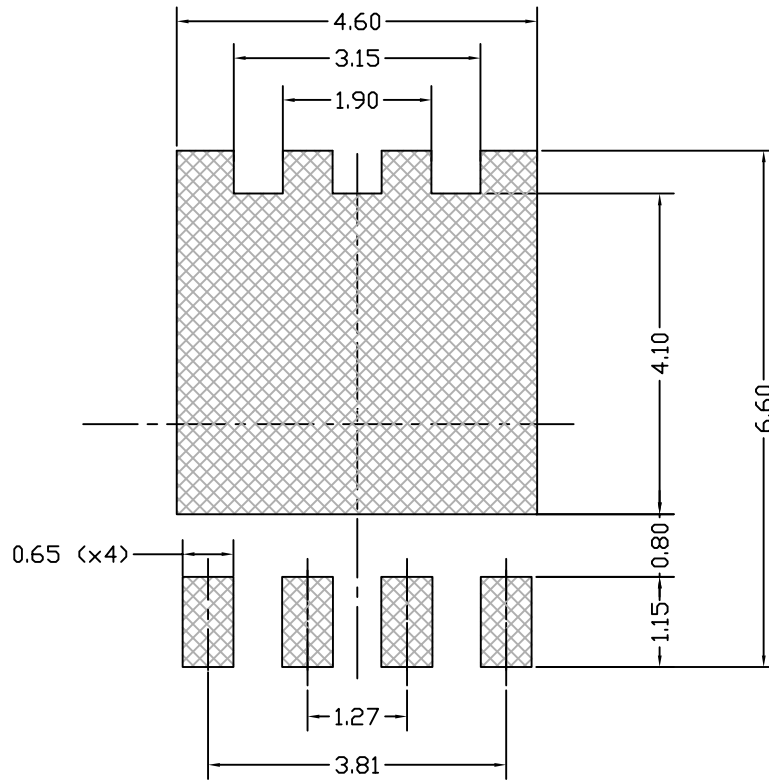


8231817\_typeC\_Rev18

**Table 8. PowerFLAT 5x6 type C package mechanical data**

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
C	5.80	6.00	6.20
D	5.00	5.20	5.40
D2	4.15		4.45
D3	4.05	4.20	4.35
D4	4.80	5.00	5.20
D5	0.25	0.40	0.55
D6	0.15	0.30	0.45
e		1.27	
E	5.95	6.15	6.35
E2	3.50		3.70
E3	2.35		2.55
E4	0.40		0.60
E5	0.08		0.28
E6	0.20	0.325	0.45
E7	0.75	0.90	1.05
K	1.05		1.35
L	0.725		1.025
L1	0.05	0.15	0.25
θ	0°		12°

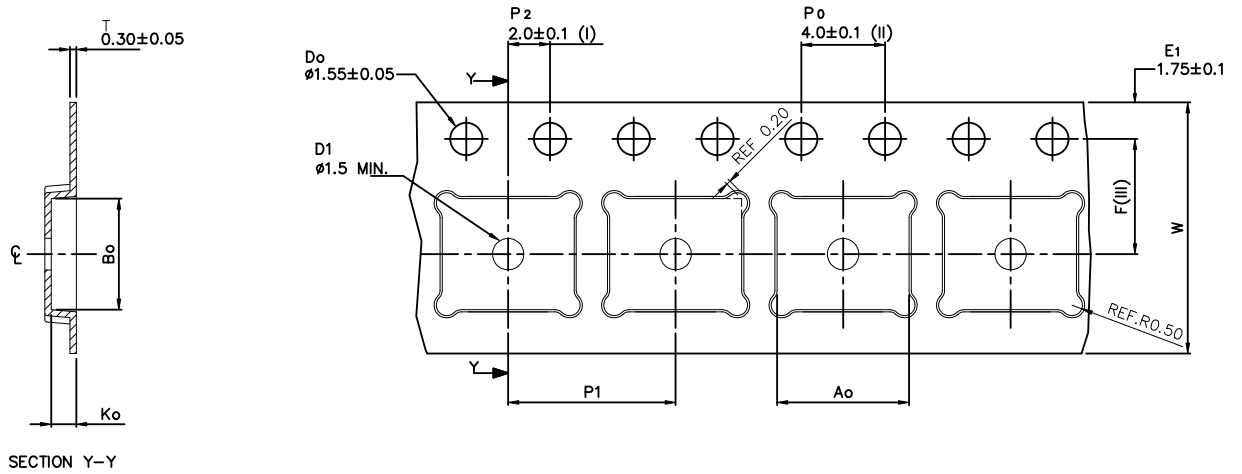
Figure 20. PowerFLAT 5x6 recommended footprint (dimensions are in mm)



8231817\_FOOTPRINT\_simp\_Rev\_18

### 4.3 PowerFLAT 5x6 packing information

Figure 21. PowerFLAT 5x6 tape (dimensions are in mm)



A <sub>0</sub>	6.30 +/- 0.1
B <sub>0</sub>	5.30 +/- 0.1
K <sub>0</sub>	1.20 +/- 0.1
F	5.50 +/- 0.1
P <sub>1</sub>	8.00 +/- 0.1
W	12.00 +/- 0.3

(I) Measured from centreline of sprocket hole to centreline of pocket.

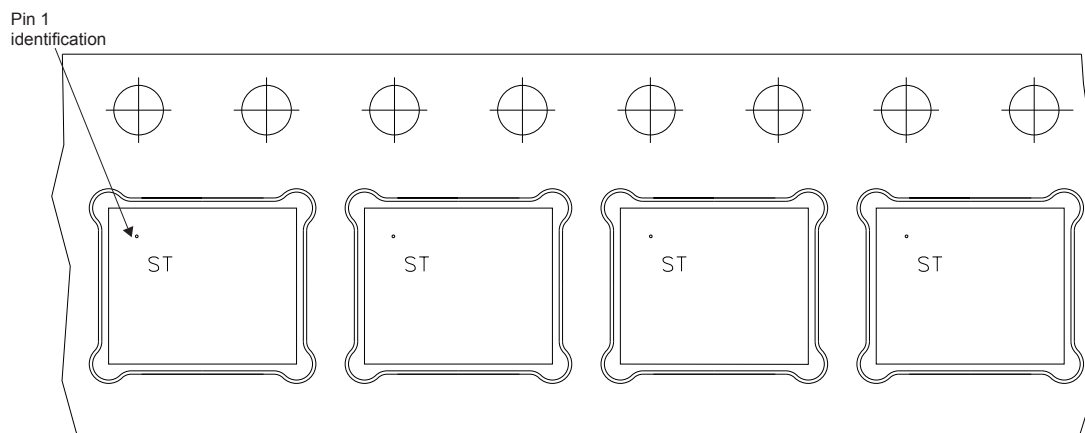
(II) Cumulative tolerance of 10 sprocket holes is  $\pm 0.20$ .

(III) Measured from centreline of sprocket hole to centreline of pocket

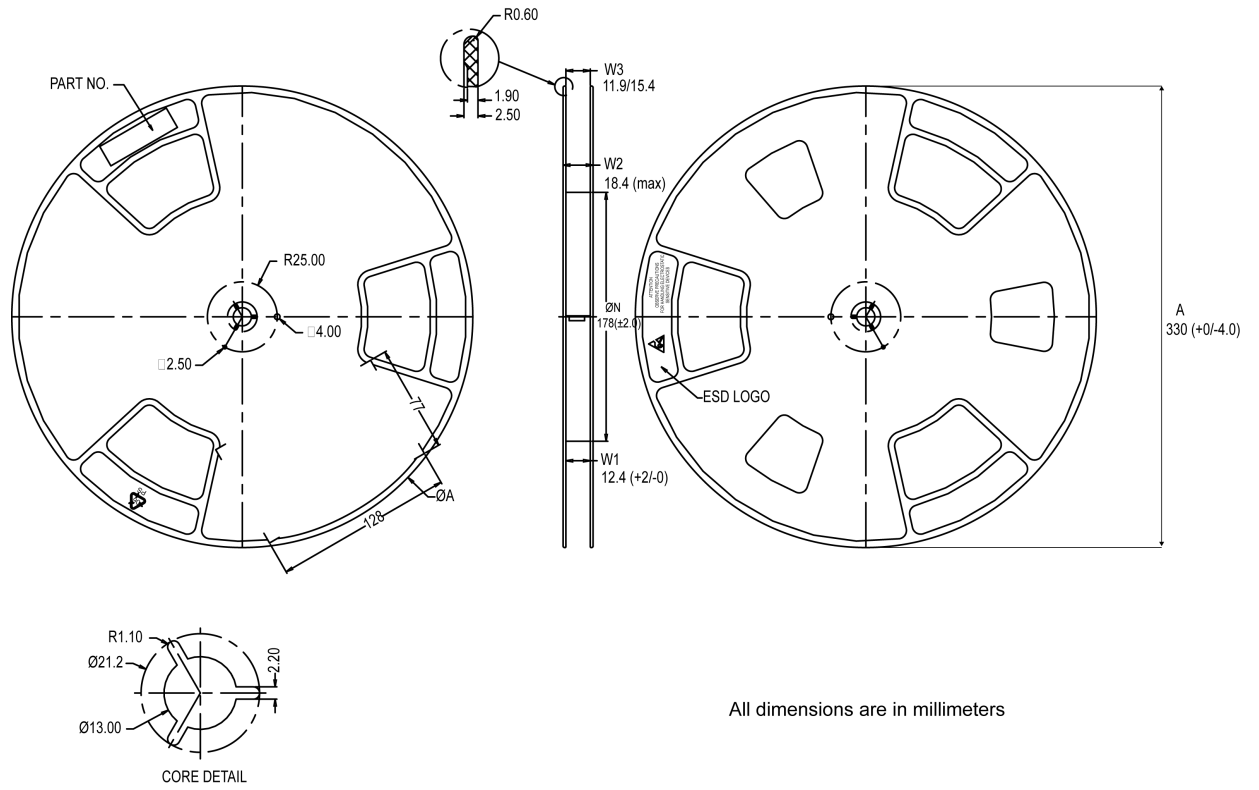
Base and bulk quantity 3000 pcs  
All dimensions are in millimeters

8234350\_Tape\_rev\_C

Figure 22. PowerFLAT 5x6 package orientation in carrier tape



**Figure 23. PowerFLAT 5x6 reel**



All dimensions are in millimeters

8234350\_Reel\_rev\_C

## Revision history

**Table 9. Document revision history**

Date	Revision	Changes
21-Oct-2014	1	Initial release.
03-Nov-2015	2	Modified: Table 2: "Absolute maximum ratings" , Table 5: "Dynamic", Table 6: "Switching times" and Table 7: "Source drain diode". Added: Section 4.1: "Electrical characteristics (curves)". Minor text changes
03-Dec-2015	3	Document status promoted from preliminary to production data.
27-Nov-2019	4	Added <a href="#">Section 4.1 PowerFLAT 5x6 type C SUBCON package information</a> . Updated <a href="#">Section 4.2 PowerFLAT 5x6 type C package information</a> . Minor text changes.



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## Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>2</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>3</b>
<b>2.1</b>	Electrical characteristics (curves) .....	5
<b>3</b>	<b>Test circuits</b> .....	<b>7</b>
<b>4</b>	<b>Package information</b> .....	<b>8</b>
<b>4.1</b>	PowerFLAT 5x6 type C SUBCON package information .....	8
<b>4.2</b>	PowerFLAT 5x6 type C package information .....	10
<b>4.3</b>	PowerFLAT™ 5x6 type C packing information .....	13
	<b>Revision history</b> .....	<b>16</b>

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